TOSHIBA Transistor Silicon PNP Epitaxial Type (PCT Process)

2SA1360

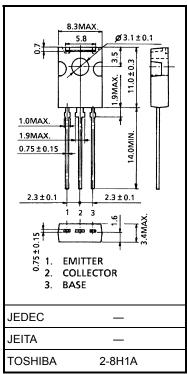
Audio Frequency Amplifier Applications

Unit: mm

- Complementary to 2SC3423
- Small collector output capacitance: $C_{ob} = 2.5 \text{ pF (typ.)}$
- High transition frequency: fT = 200 MHz (typ.)

Maximum Ratings (Tc = 25°C)

Characteristics		Symbol	Rating	Unit	
Collector-base voltage		V_{CBO}	-150	V	
Collector-emitter voltage		V _{CEO}	-150	٧	
Emitter-base voltage		V _{EBO}	-5	V	
Collector current		I _C	-50	mA	
Base current		Ι _Β	-5	mA	
Collector power dissipation	Ta = 25°C	Pc	1.2	W	
	Tc = 25°C	1.0	5		
Junction temperature		Tj	150	°C	
Storage temperature range		T _{stg}	-55 to 150	°C	



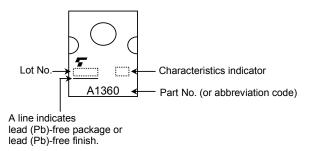
Weight: 0.82 g (typ.)

Electrical Characteristics (Tc = 25°C)

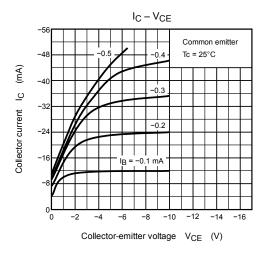
Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Collector cut-off current	I _{CBO}	V _{CB} = −150 V, I _E = 0	_	_	-0.1	μΑ
Emitter cut-off current	I _{EBO}	$V_{EB} = -5 \text{ V}, I_{C} = 0$	_	_	-0.1	μA
Collector-emitter breakdown voltage	V _(BR) CEO	$I_C = -1 \text{ mA}, I_B = 0$	-150	_	_	٧
DC current gain	h _{FE} (Note)	V _{CE} = -5 V, I _C = -10 mA	80	_	240	
Collector-emitter saturation voltage	V _{CE} (sat)	I _C = -10 mA, I _B = -1 mA	_	_	-1.0	V
Base-emitter voltage	V _{BE}	$V_{CE} = -5 \text{ V, } I_{C} = -10 \text{ mA}$	_	_	-0.8	V
Transition frequency	f _T	$V_{CE} = -5 \text{ V, } I_{C} = -10 \text{ mA}$	_	200	_	MHz
Collector output capacitance	C _{ob}	V _{CB} = −10 V, I _E = 0, f = 1 MHz	_	2.5	_	pF

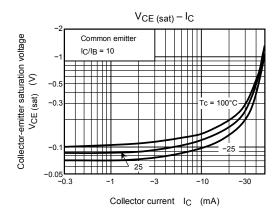
Note: hFE classification O: 80 to 160, Y: 120 to 240

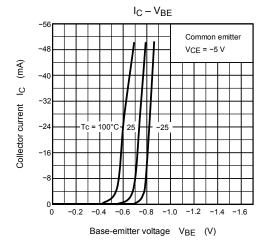
Marking

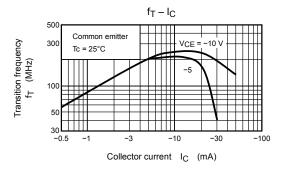


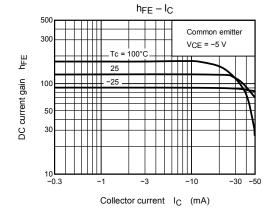
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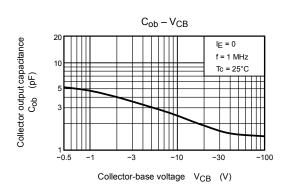




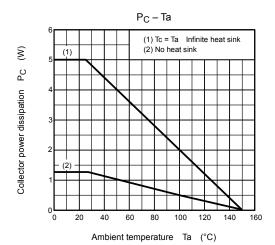








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